ABSTRACT

There is provided a configuration which improves an in-plane film thickness uniformity of a film formed on a substrate. There is included that a ~~process gas~~ first nozzle configured to supply a process gas to a process chamber that processes a substrate; a ~~n inert gas~~second nozzle arranged to be spaced apart by a predetermined distance from the ~~process gas~~ first nozzle in a circumferential direction of the substrate and configured to supply an inert gas to the process chamber; and a reaction ~~tube~~ container defining the process chamber therein and including a first protrusion protruding outward to accommodate the ~~process gas~~ first nozzle and a second protrusion protruding outward to accommodate the ~~inert gas~~ second nozzle, wherein the inert gas supplied from the ~~inert gas~~ second nozzle is supplied toward the ~~process gas~~ first nozzle to cause a flow direction of the process gas to be oriented toward the substrate.

FIG. 2